Precision Micro-Power Shunt Voltage References

Description

LM4040 and LM4041 are precision two-terminal shunt mode voltage references offered in factory programmed reverse breakdown voltages of 1.225 V, 2.500 V, 3.000 V, 3.300 V, 4.096 V, and 5.000 V.

ON Semiconductor's Charge Programmable floating gate technology ensures precise voltage settings offering five grades of initial accuracy; from 0.1% to 2%.

LM4040 and LM4041 operate over a shunt current range of $60~\mu A$ to 15 mA with low dynamic impedance, and 100 ppm/°C temperature coefficient ensuring stable reverse breakdown voltage accuracy over a wide range of operating conditions.

These shunt regulators do not require an external stabilizing capacitor but are stable with any capacitive load (up to 1 µF).

Offered in space saving SOT-23 and SC-70 packages LM4040 and LM4041 are specified for operation over the full industrial temperature range of -40° C to $+85^{\circ}$ C.

Features

- Reverse Breakdown Voltages:
 - ♦ 1.225 V
 - ♦ 2.500 V
 - ♦ 3.000 V
- ♦ 4.096 V ♦ 5.000 V

◆ D: ±1.0%

♦ E: ±2.0%

♦ 3.300 V

- Accuracy Grades:
 - ♦ A: ±0.1%
 - ◆ B: ±0.2%
 - ♦ C: ±0.5%
- Operating Current: 60 μA to 15 mA
- Low Output Noise: 35 μV
 - (10 Hz to 10 KHz)
- Small Package Size: SOT-23, SC-70
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Typical Applications

- Mobile Handheld Devices
- Industrial Process Control
- Instrumentation
- Laptop and Desktop PCs
- Automotive
- Energy Management



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SOT-23 3 Lead **TB SUFFIX CASE 527AG**



SC-70 5 Lead **SD SUFFIX** CASE 419AC

MARKING DIAGRAMS



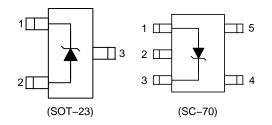


= Specific Device Code 4x (4L = LM4040, 4M = LM4041)

= Assembly Location Code Α

= Production Year = Production Month M = Pb-Free Package

PIN CONNECTIONS



ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 10 of this data sheet.

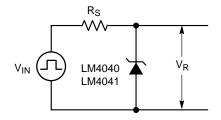


Figure 1. Test Circuit

Table 1. PIN DESCRIPTIONS

Pir	1		
SOT-23	SC-70	Name	Function
1	3	V+	Positive voltage
2	1	V-	Negative voltage
3	2	NC	This pin must be left floating or connected to V
	4	NIC	No Internal Connection. A voltage or signal applied to this pin will have no effect.
	5	NIC	7

Table 2. ABSOLUTE MAXIMUM RATINGS

	Parameter	Rating	Unit
Reverse Current		20	mA
Forward Current		10	mA
Junction Temperature		150	°C
Power Dissipation	SOT-23-3	300	mW
Power Dissipation	SC-70-5	240	mW

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Table 3. RECOMMENDED OPERATING CONDITIONS

Parameter	Rating	Unit
IREVERSE	0.06 – 15	mA
Ambient Temperature Range	-40 to +85	°C

Table 4. ESD SUSCEPTABILITY

Symbol	Parameter	Min	Units
ESD	Human Body Model	2000	V
	Machine Model	200	V

Table 5. DC ELECTRICAL CHARACTERISTICS

(IR = 100 μ A, TA = -40°C to +85°C, unless otherwise noted. Typical values are at TA = +25°C.)

					Limits		
Symbol	Parameter	Test Conditions		Min	Тур	Max	Units
1.225 V							
V_{R}	Reverse Breakdown Voltage	T _A = +25°C	LM4041A (0.1%)	1.2238	1.225	1.2262	V
			LM4041B (0.2%)	1.2226	1.225	1.2274	1
			LM4041C (0.5%)	1.219	1.225	1.231	1
			LM4041D (1.0%)	1.213	1.225	1.237	1
			LM4041E (2.0%)	1.200	1.225	1.250	
V _R	Reverse Breakdown Voltage	LM4041A	•		±1.2	±9.2	mV
	Tolerance	LM4041B			±2.4	±10.4	
		LM4041C			±6	±14	
		LM4041D			±12	±24	
		LM4041E			±25	±36	
I _{R_MIN}	Minimum Operating Current				45	65	μΑ
$\Delta V_R/\Delta T$	Reverse Breakdown Voltage	I _R = 10 mA			±20		ppm/°C
	Temperature Coefficient	I _R = 1 mA	LM4041A, B, C		±15	±100	
			LM4041D, E		±15	±150	1
		I _R = 100 μA	I _R = 100 μA		±15		
$\Delta V_R / \Delta I_R$	Reverse Breakdown Voltage	$I_{R_MIN} \le I_R \le$	LM4041A, B, C		0.7	2.0	mV
	Change with Operating Current	1 mA	LM4041D, E		0.7	2.5	
		1 mA ≤ I _R ≤	LM4041A, B, C		2.5	8	
		15 mA	LM4041D, E		2.5	10	
Z _R	Reverse Dynamic Impedance	$I_R = 1 \text{ mA},$	LM4041A, B		0.5	1.5	Ω
		f = 120 Hz, $I_{AC} = 0.1 I_{R}$	LM4041C		0.5	1.5	1
			LM4041D, E		0.5	2.0	1
e _N	Wideband Noise	I _R = 100 μA, 10	$Hz \le f \le 10 \text{ KHz}$		200		μV_{RMS}
ΔV_{R}	Reverse Breakdown Voltage Long Term Stability	T = 1000 h			120		ppm
V _{HYST}	Thermal Hysteresis (Note 2)	$\Delta T = -40^{\circ} C$ to -	+125°C		0.08		%
2.500 V				•		•	•
V _R	Reverse Breakdown Voltage	T _A = +25°C	LM4040A (0.1%)	2.498	2.500	2.502	V
			LM4040B (0.2%)	2.496	2.500	2.504	
			LM4040C (0.5%)	2.490	2.500	2.510	
			LM4040D (1.0%)	2.475	2.500	2.525	
			LM4040E (2.0%)	2.450	2.500	2.550	1
V _R	Reverse Breakdown Voltage	LM4040A	•		±2	±19	mV
	Tolerance	LM4040B			±4	±21	1
		LM4040C			±10	±29	1
		LM4040D			±25	±49	1
		LM4040E			±50	±74	1

Guaranteed by design.
 Thermal hysteresis is defined as the difference in voltage measured at +25°C after cycling to temperature -40°C and the 25°C measurement after cycling to temperature +125°C.

Table 5. DC ELECTRICAL CHARACTERISTICS

(IR = 100 μ A, TA = -40°C to +85°C, unless otherwise noted. Typical values are at TA = +25°C.)

					Limits		
Symbol	Parameter	Test (Test Conditions		Тур	Max	Units
2.500 V							
I _{R_MIN}	Minimum Operating Current				45	65	μΑ
$\Delta V_R/\Delta T$	Reverse Breakdown Voltage	I _R = 10 mA			±20		ppm/°C
	Temperature Coefficient	I _R = 1 mA	LM4040A, B, C		±15	±100	
			LM4040D, E		±15	±150	
		I _R = 100 μA			±15		
$\Delta V_R / \Delta I_R$	Reverse Breakdown Voltage	$I_{R_MIN} \le I_R \le$	LM4040A, B, C		0.3	1.0	mV
	Change with Operating Current	1 mA	LM4040D, E		0.3	1.2	
		1 mA ≤ I _R ≤	LM4040A, B, C		2.5	8	
		15 mA	LM4040D, E		2.5	10	
Z _R	Reverse Dynamic Impedance	$I_R = 1 \text{ mA},$	LM4040A, B		0.3	0.8	Ω
		f = 120 Hz, $I_{AC} = 0.1 I_{R}$	LM4040C		0.3	0.9	1
		7.0	LM4040D, E		0.3	1.1	1
e _N	Wideband Noise	I _R = 100 μA, 10	Hz ≤ f ≤ 10 KHz		350		μV _{RMS}
ΔV_{R}	Reverse Breakdown Voltage Long Term Stability	T = 1000 h			120		ppm
V _{HYST}	Thermal Hysteresis (Note 2)	$\Delta T = -40^{\circ} C$ to	$\Delta T = -40^{\circ}C \text{ to } +125^{\circ}C$		0.08		%
3.000 V		•		I.	1	<u>I</u>	
V _R	Reverse Breakdown Voltage	T _A = +25°C	LM4040A (0.1%)	2.997	3.000	3.003	V
			LM4040B (0.2%)	2.994	3.000	3.006	
			LM4040C (0.5%)	2.985	3.000	3.015	
			LM4040D (1.0%)	2.970	3.000	3.030	
			LM4040E (2.0%)	2.940	3.000	3.060	1
V _R	Reverse Breakdown Voltage	LM4040A	•		±3	±22	mV
	Tolerance	LM4040B			±6	±26	
		LM4040C			±15	±34	
		LM4040D			±30	±59	
		LM4040E			±60	±89	
I _{R_MIN}	Minimum Operating Current				45	65	μΑ
$\Delta V_R/\Delta T$	Reverse Breakdown Voltage	I _R = 10 mA			±20		ppm/°(
	Temperature Coefficient	I _R = 1 mA	LM4040A, B, C		±15	±100	1
	LM4040D, E			±15	±150		
		I _R = 100 uA			±15		1
$\Delta V_R / \Delta I_R$	Reverse Breakdown Voltage	$I_{R_MIN} \le I_R \le$	LM4040A, B, C		0.4	1.1	mV
	Change with Operating Current	1 mA	LM4040D, E		0.4	1.3	
		$1mA \le I_R \le$	LM4040A, B, C		2.7	9	
		15 mA	LM4040D, E		2.7	11	1

Guaranteed by design.
 Thermal hysteresis is defined as the difference in voltage measured at +25°C after cycling to temperature -40°C and the 25°C measurement after cycling to temperature +125°C.

Table 5. DC ELECTRICAL CHARACTERISTICS ($I_R = 100 \mu A$, $T_A = -40 ^{\circ} C$ to $+85 ^{\circ} C$, unless otherwise noted. Typical values are at $T_A = +25 ^{\circ} C$.)

		Test Conditions		Limits			T
Symbol	Parameter			Min	Тур	Max	Units
3.000 V	•	•					
Z _R	Reverse Dynamic Impedance	$I_R = 1 \text{ mA},$	LM4040A, B		0.4	0.9	Ω
		f = 120 Hz, $I_{AC} = 0.1 I_{R}$	LM4040C		0.4	0.9	1
			LM4040D, E		0.4	1.2	1
e _N	Wideband Noise	I _R = 100 μA, 10) Hz ≤ f ≤ 10 KHz		350		μV_{RMS}
ΔV_{R}	Reverse Breakdown Voltage Long Term Stability	T = 1000 h			120		ppm
V _{HYST}	Thermal Hysteresis (Note 2)	$\Delta T = -40^{\circ} C$ to	+125°C		0.08		%
3.300 V							
V _R	Reverse Breakdown Voltage	T _A = +25°C	LM4040A (0.1%)	3.297	3.300	3.303	V
			LM4040B (0.2%)	3.294	3.300	3.306	1
V_R	Reverse Breakdown Voltage	T _A = +25°C	LM4040C (0.5%)	3.285	3.300	3.315	V
			LM4040D (1.0%)	3.270	3.300	3.330	1
V_R	Reverse Breakdown Voltage	LM4040A			±3	±22	mV
	Tolerance	LM4040B			±6	±26	1
		LM4040C			±15	±34	1
		LM4040D			±30	±59	<u>] </u>
I _{R_MIN}	Minimum Operating Current				45	65	μΑ
$\Delta V_R/\Delta T$	Reverse Breakdown Voltage	I _R = 10 mA			±20		ppm/°C
	Temperature Coefficient	I _R = 1 mA	LM4040A, B, C		±15	±100	1
			LM4040D		±15	±150	1
		I _R = 100 μA	•		±15		1
$\Delta V_R / \Delta I_R$	Reverse Breakdown Voltage	$I_{R_MIN} \le I_R \le$	LM4040A, B, C		0.3	1.0	mV
	Change with Operating Current	1 mA	LM4040D		0.3	1.2	
		1 mA ≤ I _R ≤	LM4040A, B, C		2.5	8	
		15 mA	LM4040D		2.5	10	1
Z _R	Reverse Dynamic Impedance	$I_R = 1 \text{ mA},$	LM4040A, B		0.3	0.8	Ω
		f = 120 Hz, $I_{AC} = 0.1 I_{R}$	LM4040C		0.3	0.9	1
			LM4040D		0.3	1.1	1
e _N	Wideband Noise	I _R = 100 μA, 10) Hz ≤ f ≤ 10 KHz		350		μV_{RMS}
ΔV_{R}	Reverse Breakdown Voltage Long Term Stability	T = 1000 h			120		ppm
V _{HYST}	Thermal Hysteresis (Note 2)	$\Delta T = -40^{\circ} C$ to	+125°C		0.08		%
1.096 V							
V _R	Reverse Breakdown Voltage	T _A = +25°C	LM4040A (0.1%)	4.092	4.096	4.100	V
			LM4040B (0.2%)	4.088	4.096	4.104	1
			LM4040C (0.5%)	4.080	4.096	4.120	1
			LM4040D (1.0%)	4.055	4.096	4.137	1

Guaranteed by design.
 Thermal hysteresis is defined as the difference in voltage measured at +25°C after cycling to temperature -40°C and the 25°C measurement after cycling to temperature +125°C.

Table 5. DC ELECTRICAL CHARACTERISTICS

(IR = 100 μ A, TA = -40°C to +85°C, unless otherwise noted. Typical values are at TA = +25°C.)

					Limits		
Symbol	Parameter	Test C	Test Conditions		Тур	Max	Units
4.096 V		•					
V _R	Reverse Breakdown Voltage	LM4040A	LM4040A		±4	±31	mV
	Tolerance	LM4040B			±8	±35	_
		LM4040C			±20	±47	_
		LM4040D			±41	±80	
I _{R_MIN}	Minimum Operating Current				45	65	μΑ
$\Delta V_R/\Delta T$	Reverse Breakdown Voltage	I _R = 10 mA			±30		ppm/°C
	Temperature Coefficient	I _R = 1 mA	LM4040A, B, C		±20	±100	
			LM4040D		±20	±150	
		I _R = 100 μA			±15		
$\Delta V_R/\Delta I_R$	Reverse Breakdown Voltage	$I_{R_MIN} \le I_R \le$	LM4040A, B, C		0.5	1.2	mV
	Change with Operating Current	1 mA	LM4040D		0.5	1.5	
		1 mA ≤ I _R ≤	LM4040A, B, C		3.0	10	
		15 mA	LM4040D		3.0	13	
Z _R	Reverse Dynamic Impedance	I _R = 1 mA, f = 120 Hz, I _{AC} = 0.1 I _R	LM4040A, B		0.5	1.0	Ω
			LM4040C		0.5	1.0	
			LM4040D		0.5	1.3	
e _N	Wideband Noise	I _R = 100 μA, 10	Hz ≤ f ≤ 10 KHz		800		μV_{RMS}
ΔV_{R}	Reverse Breakdown Voltage Long Term Stability	T = 1000 h			120		ppm
V _{HYST}	Thermal Hysteresis (Note 2)	$\Delta T = -40^{\circ} C$ to	+125°C		0.08		%
5.000 V							
V_{R}	Reverse Breakdown Voltage	T _A = +25°C	LM4040A (0.1%)	4.995	5.000	5.005	V
			LM4040B (0.2%)	4.990	5.000	5.010	
			LM4040C (0.5%)	4.975	5.000	5.025	
			LM4040D (1.0%)	4.950	5.000	5.050	
V_{R}	Reverse Breakdown Voltage	LM4040A			±5	±38	mV
	Tolerance	LM4040B			±10	±43	
		LM4040C			±25	±58	
		LM4040D			±50	±99	
I _{R_MIN}	Minimum Operating Current				45	65	μΑ
$\Delta V_R/\Delta T$	Reverse Breakdown Voltage	I _R = 10 mA			±30		ppm/°C
	Temperature Coefficient	I _R = 1 mA	LM4040A, B, C		±20	±100	
			LM4040D		±20	±150	
		I _R = 100 μA			±15		

^{1.} Guaranteed by design.

^{2.} Thermal hysteresis is defined as the difference in voltage measured at +25°C after cycling to temperature -40°C and the 25°C measurement after cycling to temperature +125°C.

Table 5. DC ELECTRICAL CHARACTERISTICS

(IR = 100 μ A, TA = -40 °C to +85 °C, unless otherwise noted. Typical values are at TA = +25 °C.)

					Limits		
Symbol	Parameter	Test (Test Conditions		Тур	Max	Units
5.000 V							
$\Delta V_R / \Delta I_R$	Reverse Breakdown Voltage	$I_{R_MIN} \le I_R \le$	LM4040A, B, C		0.5	1.4	mV
	Change with Operating Current	1 mA	LM4040D		05	1.8	
		1 mA ≤ I _R ≤	LM4040A, B, C		3.5	12	
		15 mA	LM4040D		3.5	15	
Z _R	Reverse Dynamic Impedance	$I_R = 1 \text{ mA},$	LM4040A, B		0.5	1.1	Ω
		f = 120 Hz, $I_{AC} = 0.1 I_{R}$	LM4040C		0.5	1.1	
			LM4040D		0.5	1.5	
e _N	Wideband Noise	$I_R = 100 \mu A, 10 Hz \le f \le 10 KHz$			800		μV_{RMS}
ΔV_{R}	Reverse Breakdown Voltage Long Term Stability	T = 1000 h			120		ppm
V _{HYST}	Thermal Hysteresis (Note 2)	$\Delta T = -40^{\circ} C$ to	+125°C		0.08		%

Guaranteed by design.
 Thermal hysteresis is defined as the difference in voltage measured at +25°C after cycling to temperature -40°C and the 25°C measurement after cycling to temperature +125°C.

TYPICAL PERFORMANCE CHARACTERISTICS

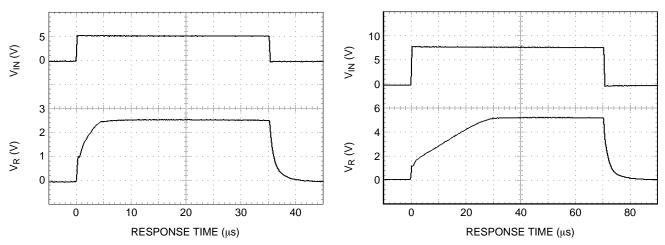


Figure 2. LM4040 $- 2.5 \text{ V } (R_S = 30 \text{ k})$

Figure 3. LM4040 – 5 V ($R_S = 30 \text{ k}$)

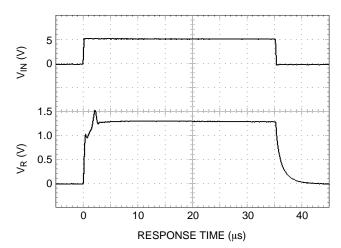


Figure 4. LM4041 – 1.225 V ($R_S = 30 \text{ k}$)

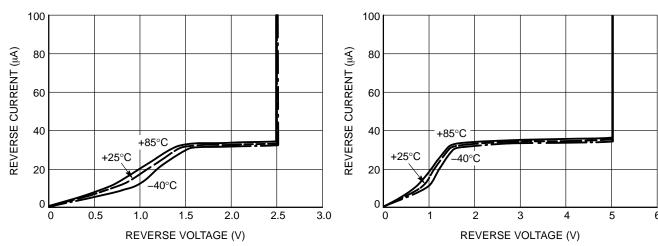


Figure 5. Reverse Characteristics (LM4040 – 2.5 V)

Figure 6. Reverse Characteristics (LM4040 – 5 V)

TYPICAL PERFORMANCE CHARACTERISTICS

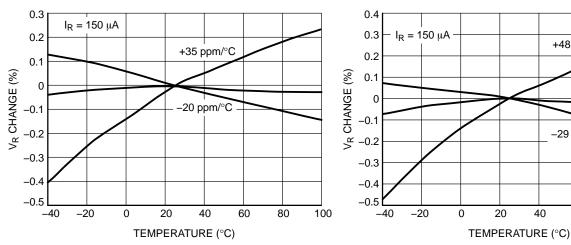


Figure 7. Temperature Drift - LM4040

Figure 8. Temperature Drift - LM4041

40

+48 ppm/°C

-29 ppm/°C

60

100

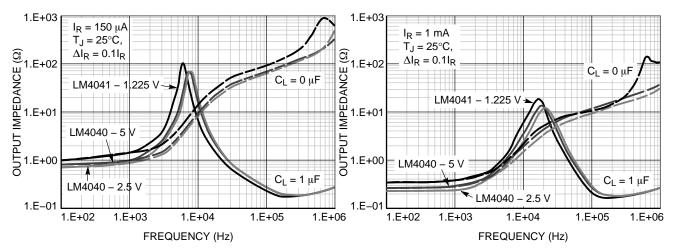


Figure 9. Output Impedance vs. Frequency

Figure 10. Output Impedance vs. Frequency

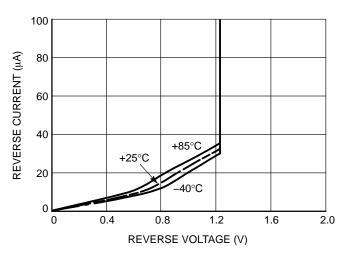


Figure 11. Reverse Characteristics - LM4041

Device Description

The LM404x shunt references use ON Semiconductor's floating gate (EEPROM) technology to produce a capacitor which stores an accurate and stable voltage that is used as the reference voltage for a control amplifier and shunt N-channel FET.

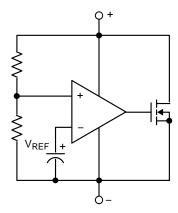


Figure 12. Functional Block Diagram

The device operates like a zener diode; maintaining a fixed voltage across its output terminals when biased with $60~\mu A$ to 15~m A of reverse current. The LM404x will also act like a silicon diode when forward biased with currents up to 10~m A.

Applications Information

The LM404x's internal pass transistor maintains a constant output voltage by sinking the necessary amount of current across a source resistor. The source resistance (RS) is set by the load current range (I_{LOAD}), supply voltage (VS) variations, LM404x's terminal voltage (VR), and desired quiescent current.

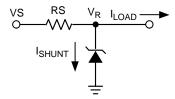


Figure 13. Typical Operating Circuit

To select a value of RS, set VS at its minimum value and $I_{\rm LOAD}$ at its maximum. Be sure to maintain a minimum operating current of 60 μA through LM404x at all times, as LM404x uses this current to power its internal circuitry. The RS value should be large enough to keep $I_{\rm SHUNT}$ less than 15 mA for proper regulation when VS is maximum and $I_{\rm LOAD}$ is at a minimum. Therefore, the value of RS is bounded by the following equation:

$$\frac{\left(V_{S(min)} - V_{R}\right)}{\left(60 \; \mu A + I_{LOAD(max)}\right)} > RS$$

and

$$RS > \frac{\left(V_{S(max)} - V_{R}\right)}{\left(15 \text{ mA} + I_{LOAD(min)}\right)}$$

Choosing a larger resistance minimizes the power dissipated in the circuit by reducing the shunt current.

Output Capacitance

The LM404x does not require an external capacitor for frequency stability and is stable for any output capacitance.

Effect of Temperature

LM404x has an output voltage temperature coefficient of typically ± 15 to ± 30 ppm/°C meaning the LM404x's output voltage will change by $50-100~\mu\text{V/°C}$ for a 3.300 V regulator. The polarity of this temperature induced voltage shift can vary from device to device, some moving in the positive direction and others in the negative direction.

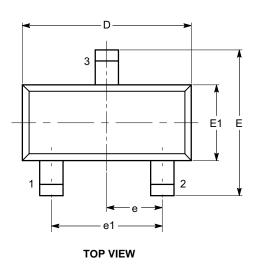
Table 6. ORDERING INFORMATION

Part Number	Specific Device Marking	Voltage	Accuracy	Max Drift	Temperature Range	Package (Note 3)
LM4040 B TB-250GT3		2.500 V	±0.2%	100 ppm/°C		
LM4040 B TB-300GT3	4L	3.000 V	±0.2%	100 ppm/°C	–40°C to 85°C	SOT-23-3
LM4040 B TB-409GT3	1 4L	4.096 V	±0.2%	100 ppm/°C	-40°C t0 65°C	301-23-3
LM4040 B TB-500GT3		5.000 V	±0.2%	100 ppm/°C		
LM4041 C SD-122GT3	4M	1.225 V	±0.5%	100 ppm/°C	-40°C to 85°C	SC-70-5

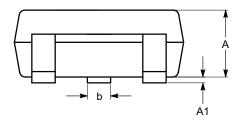
- 3. Tape & Reel, 3,000 Units / Reel
- 4. All packages are RoHS-compliant (Lead-free, Halogen-free).
- 5. The standard lead finish is NiPdAu.
- For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
- 7. For detailed information and a breakdown of device nomenclature and numbering systems, please see the ON Semiconductor Device Nomenclature document, TND310/D, available at www.onsemi.com

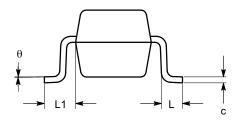
PACKAGE DIMENSIONS

SOT-23, 3 Lead CASE 527AG ISSUE O



SYMBOL	MIN	NOM	MAX		
Α	0.89		1.12		
A1	0.013		0.10		
b	0.37		0.50		
С	0.085		0.18		
D	2.80		3.04		
Е	2.10		2.64		
E1	1.20		1.40		
е		0.95 BSC			
e1		1.90 BSC			
L	0.40 REF				
L1	0.54 REF				
θ	0°		8°		





SIDE VIEW

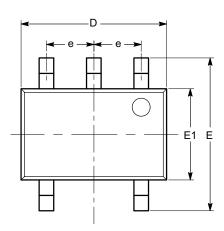
Notes:

- (1) All dimensions are in millimeters. Angles in degrees.(2) Complies with JEDEC TO-236.

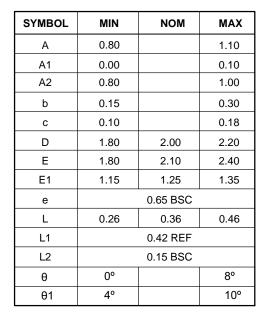
END VIEW

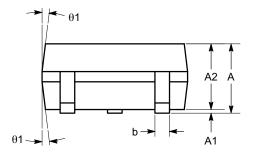
PACKAGE DIMENSIONS

SC-88A (SC-70 5 Lead), 1.25x2 CASE 419AC ISSUE A

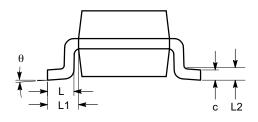


TOP '	VIE	ΞW
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SIDE VIEW



END VIEW

Notes:

- (1) All dimensions are in millimeters. Angles in degrees.
- (2) Complies with JEDEC MO-203.

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